

Phase Control Thyristors

Features

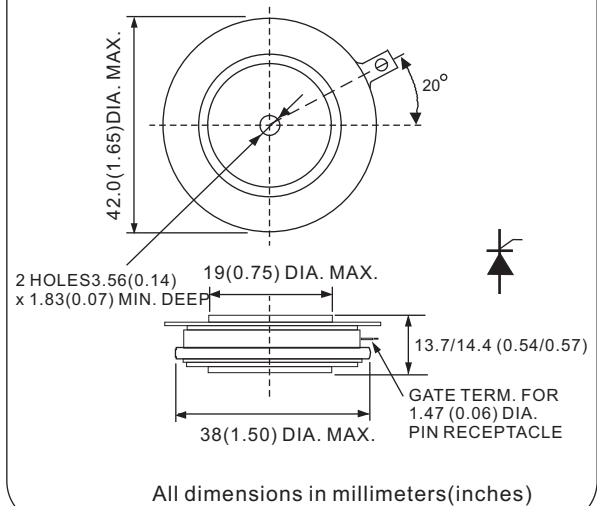
1. 340 PT series Thyristors are deigned for various power controls
2. Voltage rating up to 1600 V.
3. Typical application
 - DC motor control
 - Controlled DC power supplies
 - AC controllers

Ordering code

340	PT	xx	A	0
(1)	(2)	(3)	(4)	(5)

- (1) Maximum average on-state current , A
 (2) For Phase Control Thyristor
 (3) Voltage code , code x 100 = V_{RRM} / V_{DRM}
 (4) package style : A , B , C , D , E for Disc Type
 (5) Terminal types
 0 - for eyelet

A TYPE



Electrical Characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Type	Max.	
$I_T(AV)$	Mean on-state current	180° half sine wave , 50Hz Double side cooled , $T_C = 55^\circ C$			340	A
$I_T(RMS)$	Max. RMS on-state current	Double side cooled , $T_{HS} = 25^\circ C$			709	A
V_{RRM} V_{DRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	V_{DRM} & V_{RRM} $t_p=10ms$ V_{DSM} & $V_{RSM} = V_{DRM}$ & $V_{RRM} + 100V$	1200		1600	V
I_{TSM}	Surge on-state current	10 ms half sine wave			4200	A
I_t^2	For fusing coordination	$V_R = 0.6V_{RRM}$			107	KA ² s
$V_{T(TO)}$	Threshold voltage				1.08	V
r_t	On-state slope resistance				1.3	mΩ
V_{TM}	Max. Forward voltage drop	$I_{TM}=900A$, $F=8.0KN$			2.08	V
I_H	Holding current	$V_A=12V$, $I_A=1A$			600	mA
di/dt	Cirtical rate of rise of turned-on current	Gate drive 20V , 20Ω , $t_r \leq 0.5 \mu s$			1000	A/ μs
t_q	Typical turn-off time	$I_{TM}=400A$, $d_v/dt=30V/\mu s$ $d_iRR/dt=10 A/\mu s$			250	μs
d_v/dt	Cirtical rate of rise of off-state voltage	$V_{DM}=0.67 V_{DRM}$			1000	V/ μs
P_G	Max. average gate power	Square wave pulse width 100 μs			2	W
P_{GM}	Max. peak gate power square				30	W
I_{GT}	Gate trigger current	$V_A=12V$, $I_A=1A$			150	mA
V_{GT}	Gate trigger voltage				3	V
T_{stg}	Storage tempe rature		- 40		150	°C
T_j	Max.operating temperaturerange		- 40		125	°C
$R_{th}(j-h)$	Thermal resistance (junction to heatsink)	Double side cooled , clamp ing force 8.0 KN			0.21	°C/ W
F_m	Moun ting force		3.3		5.5	KN
W_t	Appr oximate weight			70		g

Fig. 1

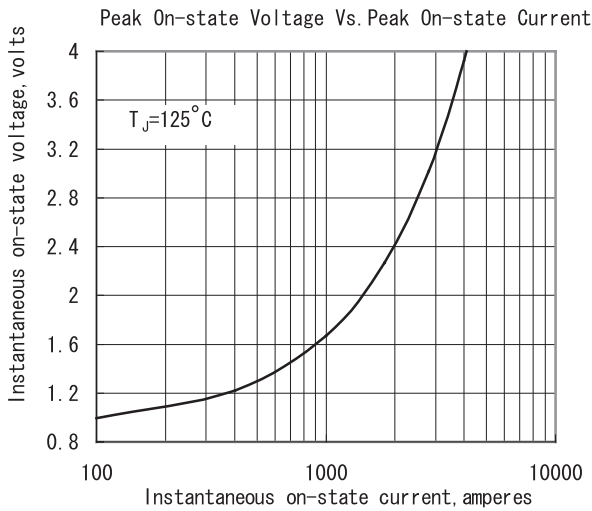


Fig. 2

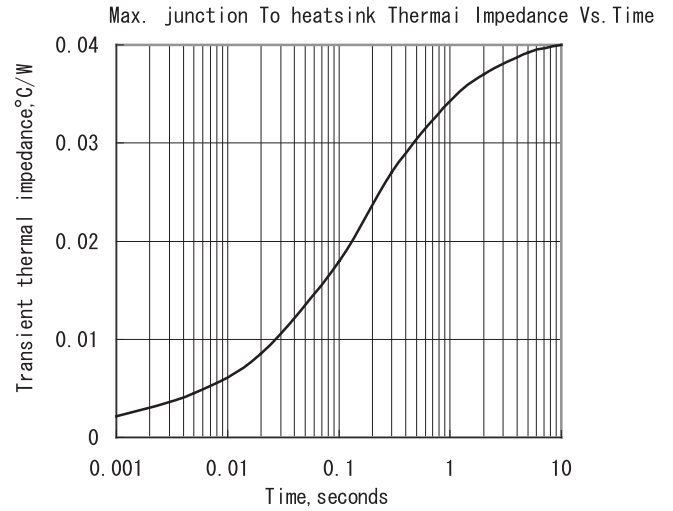


Fig. 3

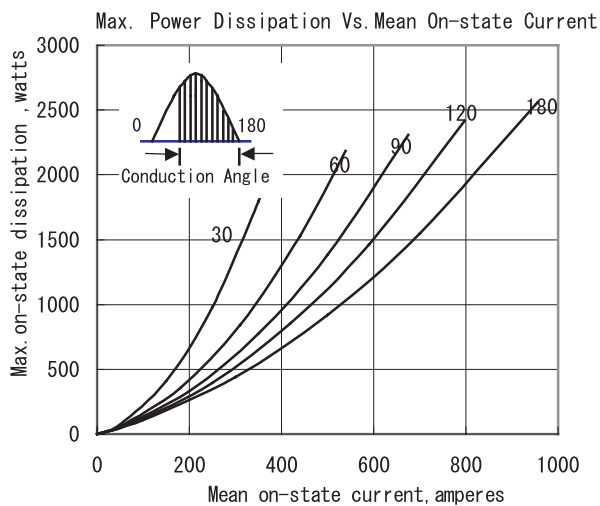


Fig. 4

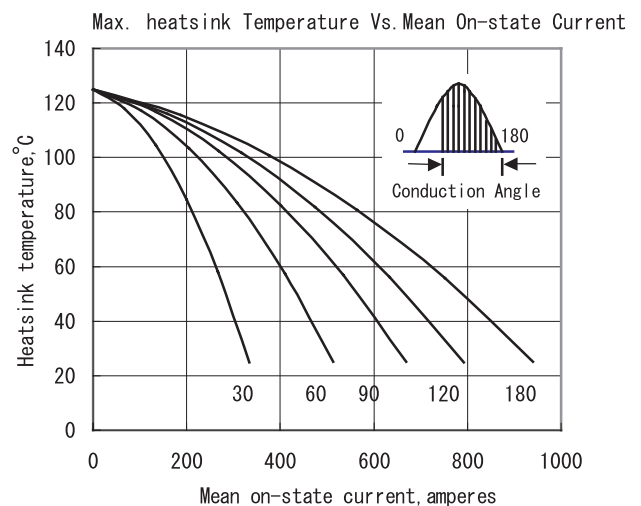


Fig. 5

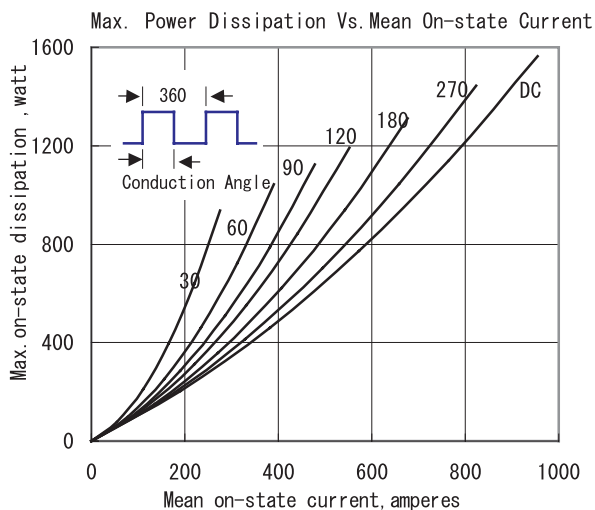


Fig. 6

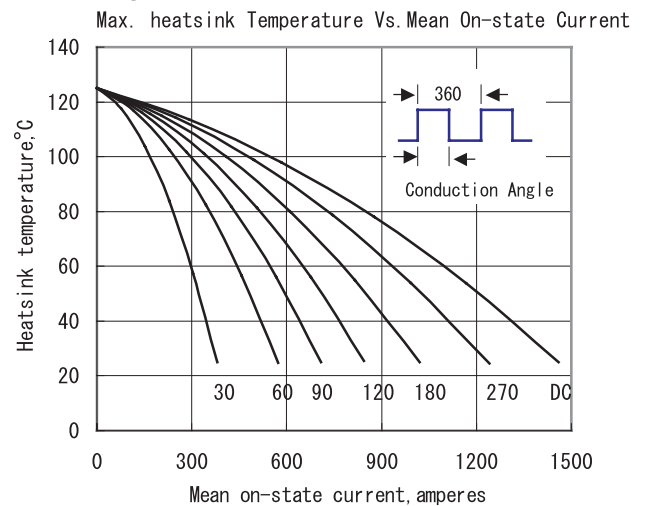


Fig. 7

Surge Current Vs. Cycles

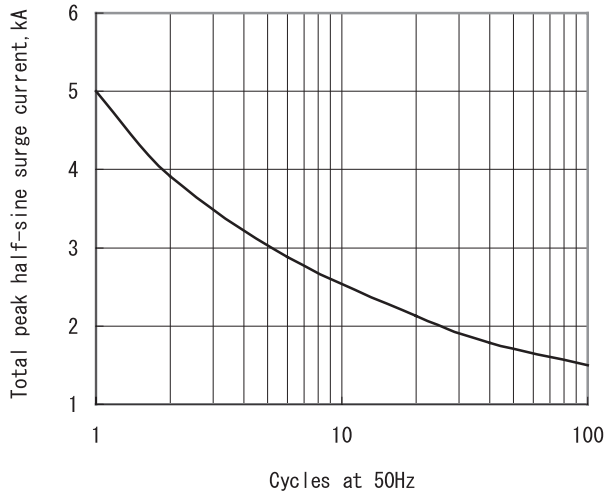


Fig. 8

I^2t Vs. Time

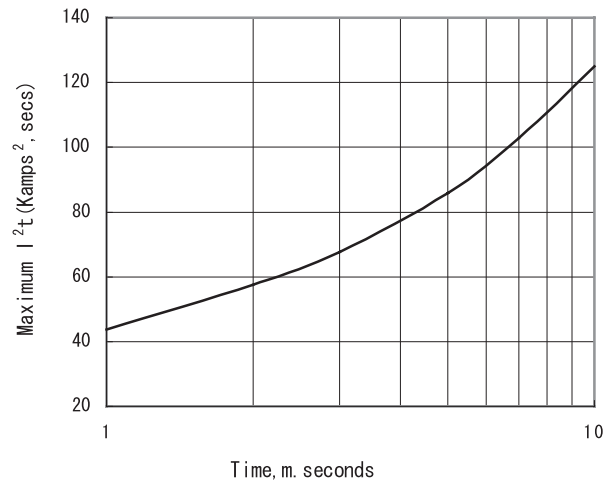


Fig. 9

Gate characteristic at 25°C junction temperature

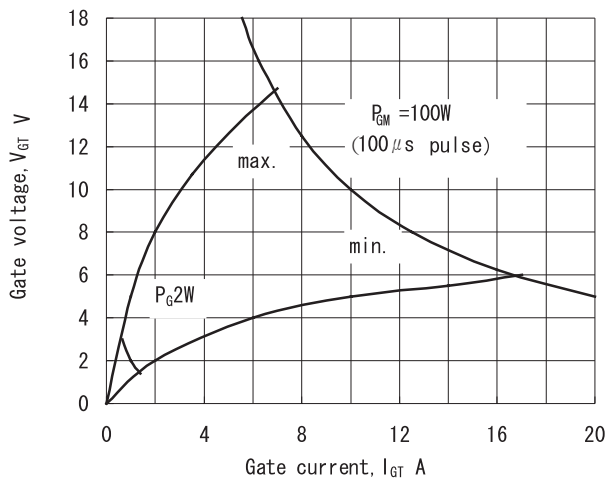


Fig. 10

Gate Trigger Zone at varies temperature

